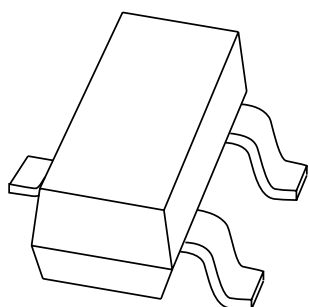


DATA SHEET



PBSS9110T

100 V, 1 A

PNP low V_{CEsat} (BISS) transistor

Product specification
Supersedes data of 2004 May 06

2004 May 13

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

PBSS9110T

FEATURES

- SOT23 package
- Low collector-emitter saturation voltage V_{CEsat}
- High collector current capability: I_C and I_{CM}
- Higher efficiency leading to less heat generation

APPLICATIONS

- Major application segments
 - Automotive 42 V power
 - Telecom infrastructure
 - Industrial
- DC-to-DC conversion
- Peripheral drivers
 - Driver in low supply voltage applications (e.g. lamps and LEDs).
 - Inductive load driver (e.g. relays, buzzers and motors).

DESCRIPTION

PNP low V_{CEsat} transistor in a SOT23 plastic package.
NPN complement: PBSS8110T.

MARKING

TYPE NUMBER	MARKING CODE ⁽¹⁾
PBSS9110T	*U7

Note

- * = p: Made in Hong Kong.
* = t: Made in Malaysia.
* = W: Made in China.

ORDERING INFORMATION

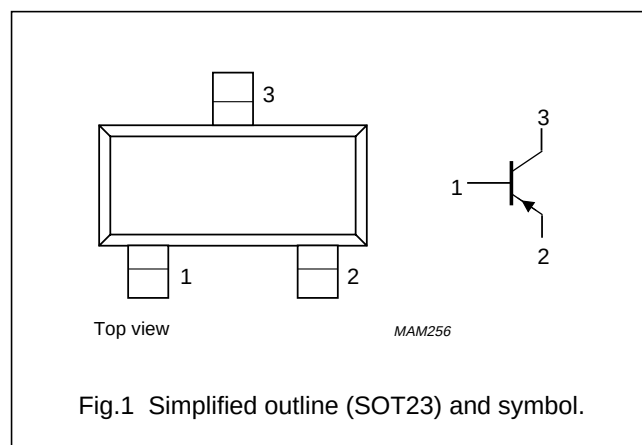
TYPE NUMBER	PACKAGE		
	NAME	DESCRIPTION	VERSION
PBSS9110T	–	plastic surface mounted package; 3 leads	SOT23

QUICK REFERENCE DATA

SYMBOL	PARAMETER	MAX.	UNIT
V_{CEO}	collector-emitter voltage	–100	V
I_C	collector current (DC)	–1	A
I_{CM}	repetitive peak collector current	–3	A
R_{CEsat}	equivalent on-resistance	320	mΩ

PINNING

PIN	DESCRIPTION
1	base
2	emitter
3	collector



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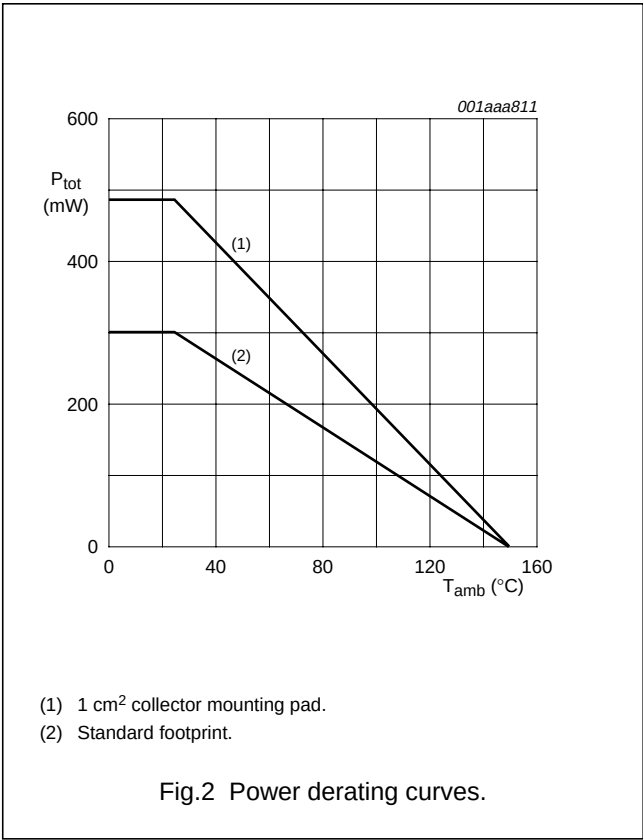
LIMITING VALUES

In accordance with the Absolute Maximum Rating System (IEC 60134).

SYMBOL	PARAMETER	CONDITIONS	MIN.	MAX.	UNIT
V_{CBO}	collector-base voltage	open emitter	–	–120	V
V_{CEO}	collector-emitter voltage	open base	–	–100	V
V_{EBO}	emitter-base voltage	open collector	–	–5	V
I_C	collector current (DC)		–	–1	A
I_{CM}	peak collector current	limited by $T_{j(max)}$	–	–3	A
I_B	base current (DC)		–	–300	mA
P_{tot}	total power dissipation	$T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 1	–	300	mW
		$T_{amb} \leq 25\text{ }^{\circ}\text{C}$; note 2	–	480	mW
T_j	junction temperature		–	150	$^{\circ}\text{C}$
T_{amb}	operating ambient temperature		–65	+150	$^{\circ}\text{C}$
T_{stg}	storage temperature		–65	+150	$^{\circ}\text{C}$

Notes

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated, standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm² collector mounting pad.



100 V, 1 A
PNP low V_{CEsat} (BISS) transistor

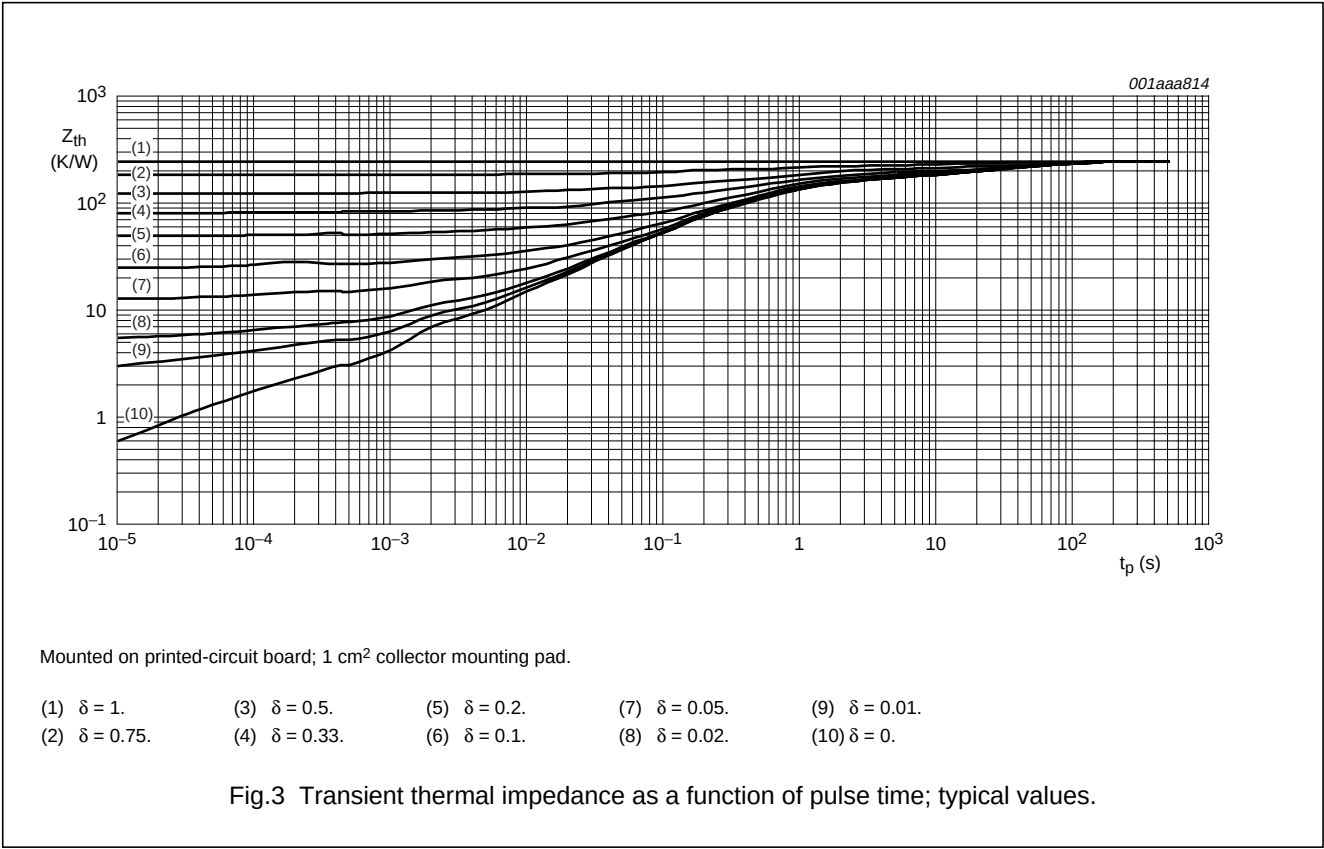
PBSS9110T

THERMAL CHARACTERISTICS

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$R_{th(j-a)}$	thermal resistance from junction to ambient	in free air; note 1	417	K/W
		in free air; note 2	260	K/W

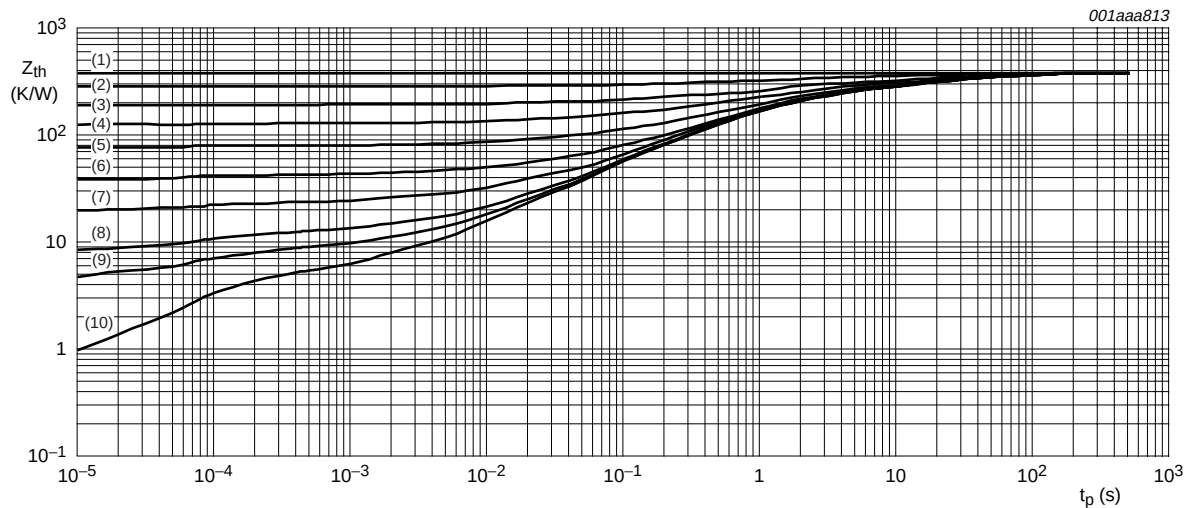
Notes

1. Device mounted on a printed-circuit board, single-sided copper, tin-plated and standard footprint.
2. Device mounted on a printed-circuit board, single-sided copper, tin-plated and 1 cm² collector mounting pad.



100 V, 1 A
PNP low V_{CEsat} (BISS) transistor

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Mounted on printed-circuit board; standard footprint.

- | | | | | |
|----------------------|----------------------|---------------------|----------------------|----------------------|
| (1) $\delta = 1.$ | (3) $\delta = 0.5.$ | (5) $\delta = 0.2.$ | (7) $\delta = 0.05.$ | (9) $\delta = 0.01.$ |
| (2) $\delta = 0.75.$ | (4) $\delta = 0.33.$ | (6) $\delta = 0.1.$ | (8) $\delta = 0.02.$ | (10) $\delta = 0.$ |

Fig.4 Transient thermal impedance as a function of pulse time; typical values.

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

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CHARACTERISTICS

$T_j = 25\text{ °C}$ unless otherwise specified.

SYMBOL	PARAMETER	CONDITIONS	MIN.	TYP.	MAX.	UNIT
I_{CBO}	collector-base cut-off current	$V_{CB} = -80\text{ V}; I_E = 0\text{ A}$	–	–	–100	nA
		$V_{CB} = -80\text{ V}; I_E = 0\text{ A}; T_j = 150\text{ °C}$	–	–	–50	μA
I_{CES}	collector-emitter cut-off current	$V_{CE} = -80\text{ V}; V_{BE} = 0\text{ A}$	–	–	–100	nA
I_{EBO}	emitter-base cut-off current	$V_{EB} = -4\text{ V}; I_C = 0\text{ A}$	–	–	–100	nA
h_{FE}	DC current gain	$V_{CE} = -5\text{ V}; I_C = -1\text{ mA}$	150	–	–	
		$V_{CE} = -5\text{ V}; I_C = -250\text{ mA}$	150	–	–	
		$V_{CE} = -5\text{ V}; I_C = -500\text{ mA}$; note 1	150	–	450	
		$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$; note 1	125	–	–	
V_{CEsat}	collector-emitter saturation voltage	$I_C = -250\text{ mA}; I_B = -25\text{ mA}$	–	–	–120	mV
		$I_C = -500\text{ mA}; I_B = -50\text{ mA}$	–	–	–180	mV
		$I_C = -1\text{ A}; I_B = -100\text{ mA}$; note 1	–	–	–320	mV
R_{CEsat}	equivalent on-resistance	$I_C = -1\text{ A}; I_B = -100\text{ mA}$; note 1	–	170	320	$\text{m}\Omega$
V_{BEsat}	base-emitter saturation voltage	$I_C = -1\text{ A}; I_B = -100\text{ mA}$	–	–	–1.1	V
V_{BEon}	base-emitter turn-on voltage	$V_{CE} = -5\text{ V}; I_C = -1\text{ A}$	–	–	–1	V
f_T	transition frequency	$V_{CE} = -10\text{ V}; I_C = -50\text{ mA}$; $f = 100\text{ MHz}$	100	–	–	MHz
C_c	collector capacitance	$V_{CB} = -10\text{ V}; I_E = I_C = 0\text{ A}$; $f = 1\text{ MHz}$	–	–	17	pF

Note

1. Pulse test: $t_p \leq 300\text{ }\mu\text{s}$; $\delta \leq 0.02$.

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

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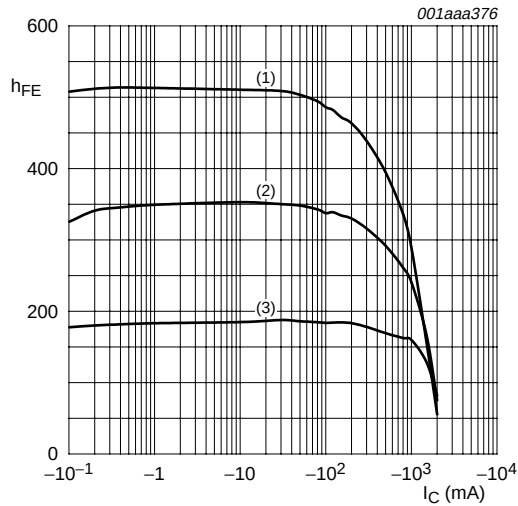
 $V_{CE} = -10$ V.(1) $T_{amb} = 100$ °C.(2) $T_{amb} = 25$ °C.(3) $T_{amb} = -55$ °C.

Fig.5 DC current gain as a function of collector current; typical values.

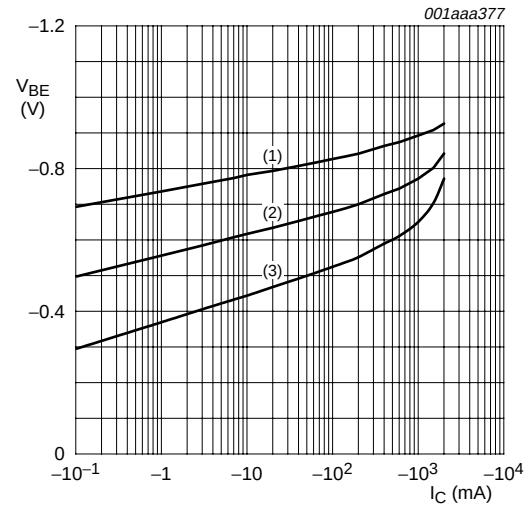
 $V_{CE} = -10$ V.(1) $T_{amb} = -55$ °C.(2) $T_{amb} = 25$ °C.(3) $T_{amb} = 100$ °C.

Fig.6 Base-emitter voltage as a function of collector current; typical values.

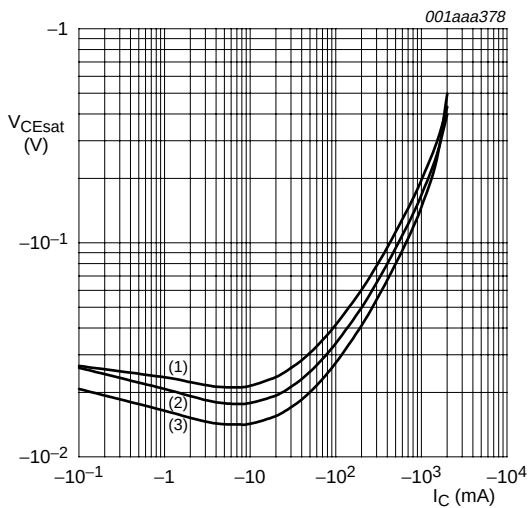
 $I_C/I_B = 10$.(1) $T_{amb} = 100$ °C.(2) $T_{amb} = 25$ °C.(3) $T_{amb} = -55$ °C.

Fig.7 Collector-emitter saturation voltage as a function of collector current; typical values.

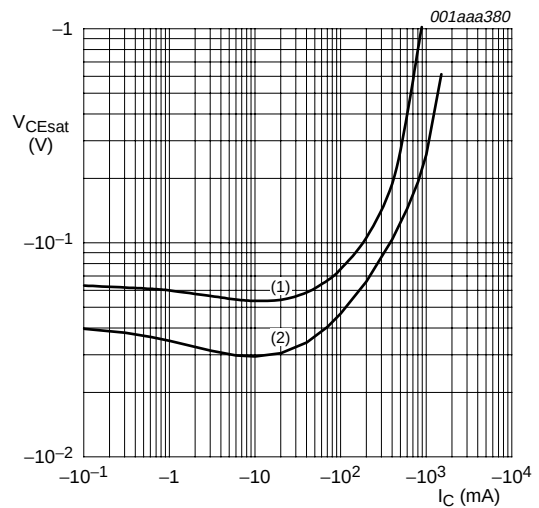
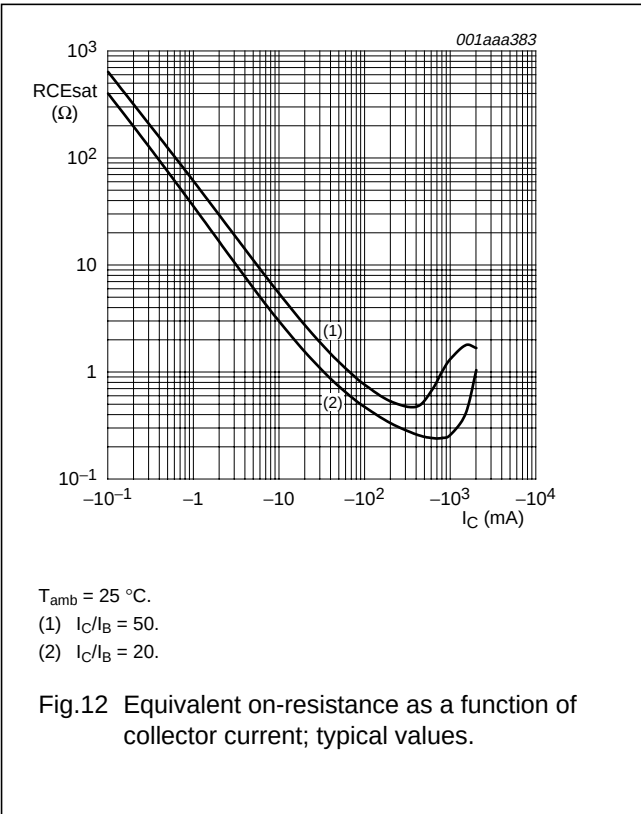
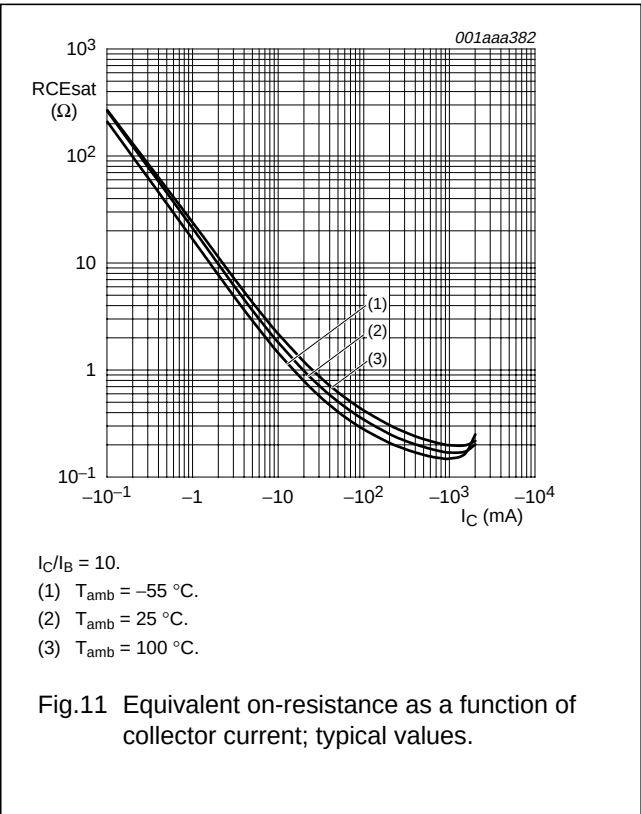
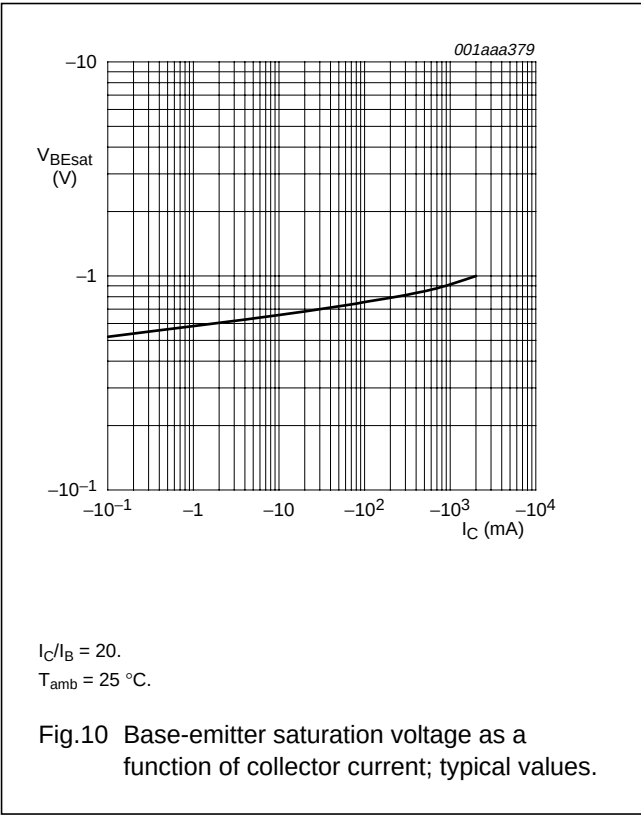
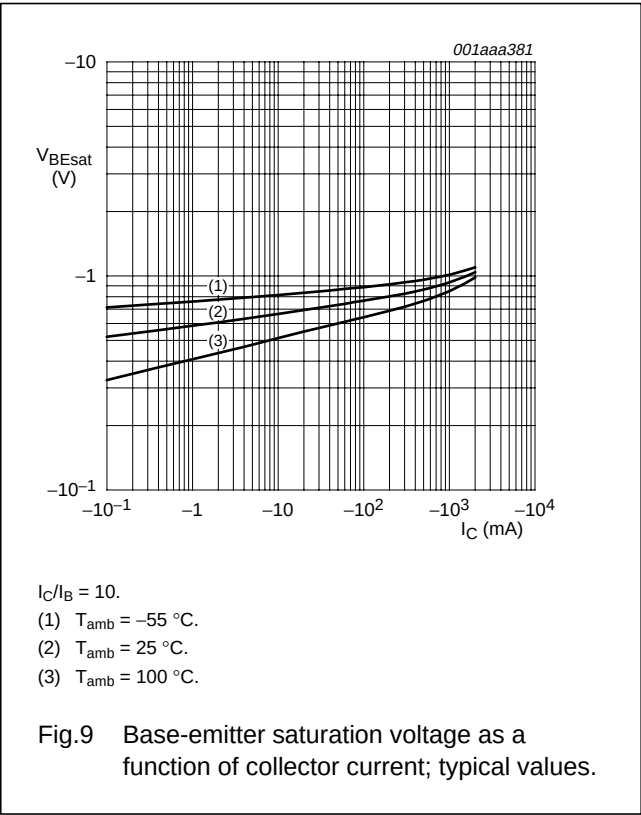
 $T_{amb} = 25$ °C.(1) $I_C/I_B = 50$.(2) $I_C/I_B = 20$.

Fig.8 Collector-emitter saturation voltage as a function of collector current; typical values.

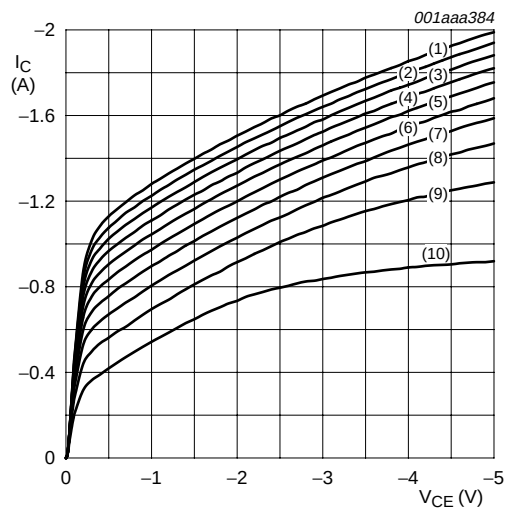
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100 V, 1 A PNP low V_{CEsat} (BISS) transistor

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$T_{amb} = 25\text{ }^{\circ}\text{C}.$

- | | | |
|-----------------------------|-----------------------------|-----------------------------|
| (1) $I_B = 45\text{ mA}.$ | (5) $I_B = 27\text{ mA}.$ | (9) $I_B = 9\text{ mA}.$ |
| (2) $I_B = 40.5\text{ mA}.$ | (6) $I_B = 22.5\text{ mA}.$ | (10) $I_B = 4.5\text{ mA}.$ |
| (3) $I_B = 36\text{ mA}.$ | (7) $I_B = 18\text{ mA}.$ | |
| (4) $I_B = 31.5\text{ mA}.$ | (8) $I_B = 13.5\text{ mA}.$ | |

Fig.13 Collector current as a function of collector-emitter voltage; typical values.

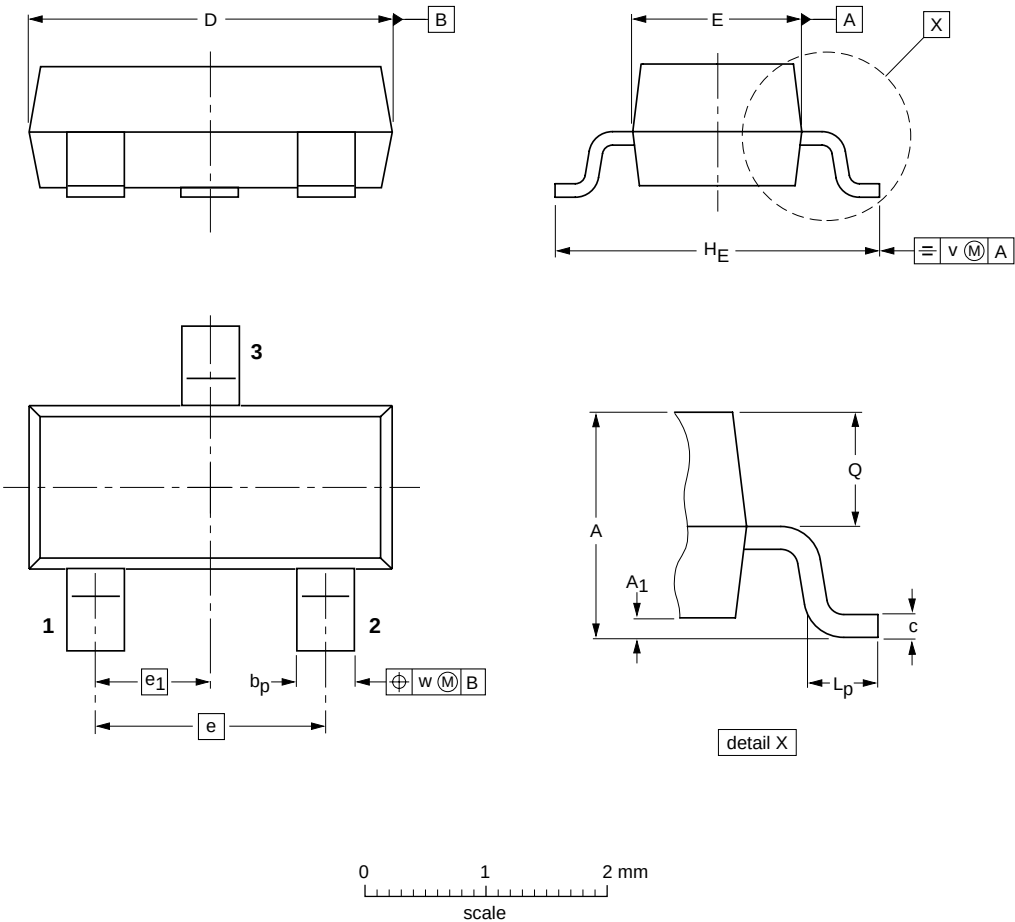
100 V, 1 A
PNP low V_{CEsat} (BISS) transistor

PBSS9110T

PACKAGE OUTLINE

Plastic surface mounted package; 3 leads

SOT23



DIMENSIONS (mm are the original dimensions)

UNIT	A	A ₁ max.	b _p	c	D	E	e	e ₁	H _E	L _p	Q	v	w
mm	1.1 0.9	0.1	0.48 0.38	0.15 0.09	3.0 2.8	1.4 1.2	1.9	0.95	2.5 2.1	0.45 0.15	0.55 0.45	0.2	0.1

OUTLINE VERSION	REFERENCES				EUROPEAN PROJECTION	ISSUE DATE
	IEC	JEDEC	EIAJ			
SOT23		TO-236AB				97-02-28 99-09-13

100 V, 1 A PNP low V_{CEsat} (BISS) transistor

PBSS9110T

DATA SHEET STATUS

LEVEL	DATA SHEET STATUS ⁽¹⁾	PRODUCT STATUS ⁽²⁾⁽³⁾	DEFINITION
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3. For data sheets describing multiple type numbers, the highest-level product status determines the data sheet status.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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